

DATA SHEET

BFG16A

NPN 2 GHz wideband transistor

Product specification
Supersedes data of November 1992
File under Discrete Semiconductors, SC14

1995 Sep 12

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FEATURES

- High power gain
- Good thermal stability
- Gold metallization ensures excellent reliability.

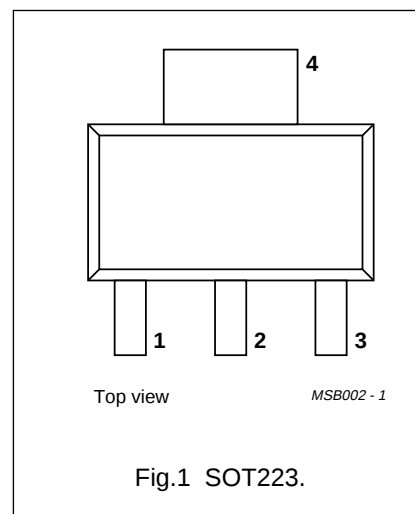
DESCRIPTION

NPN transistor mounted in a plastic SOT223 envelope.

It is primarily intended for use in wideband amplifiers, aerial amplifiers and vertical amplifiers in high speed oscilloscopes.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	—	40	V
V_{CEO}	collector-emitter voltage	open base	—	—	25	V
I_C	DC collector current		—	—	150	mA
P_{tot}	total power dissipation	up to $T_s = 110\text{ °C}$; note 1	—	—	1	W
h_{FE}	DC current gain	$I_C = 150\text{ mA}$; $V_{CE} = 5\text{ V}$; $T_j = 25\text{ °C}$	25	80	—	
f_T	transition frequency	$I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	1.5	—	GHz
G_{UM}	maximum unilateral power gain	$I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	10	—	dB

Note

1. T_s is the temperature at the soldering point of the collector tab.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	40	V
V_{CEO}	collector-emitter voltage	open base	—	25	V
V_{EBO}	emitter-base voltage	open collector	—	2	V
I_C	DC collector current		—	150	mA
P_{tot}	total power dissipation	up to $T_s = 110\text{ °C}$; note 1	—	1	W
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C

Note

1. T_s is the temperature at the soldering point of the collector tab.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 110\ ^\circ\text{C}$; note 1	40	K/W

Note

- T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

$T_j = 25\ ^\circ\text{C}$ unless otherwise specified.

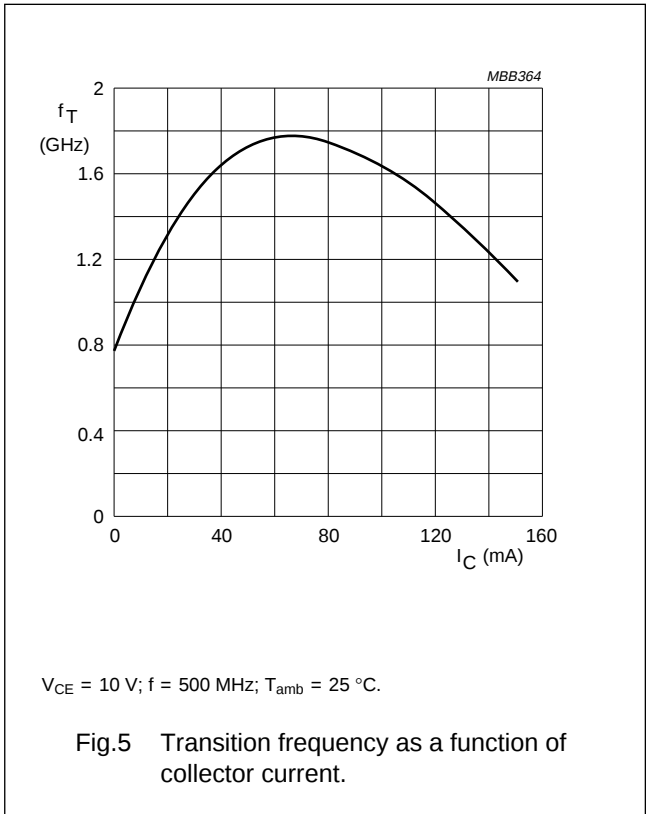
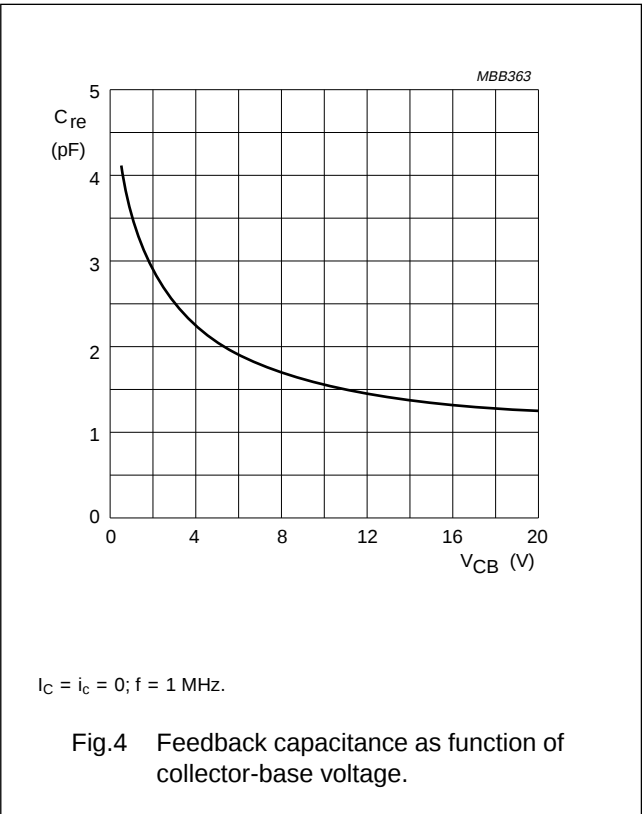
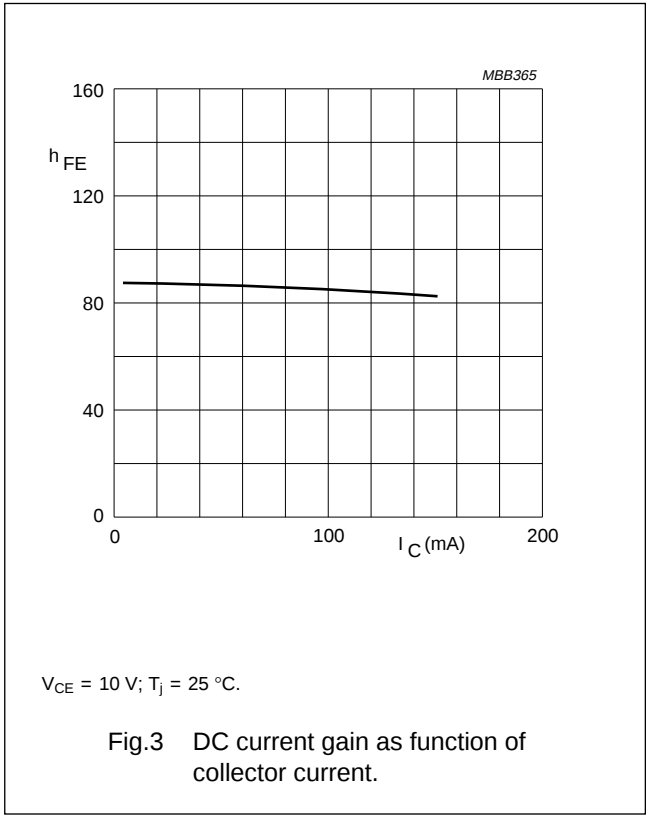
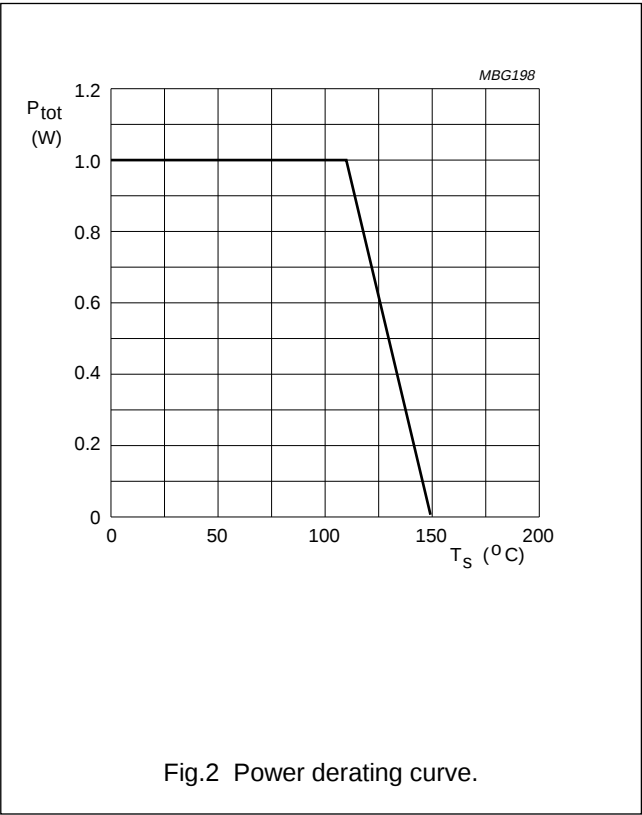
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter; $I_C = 0.1\ \text{mA}$	25	–	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	open base; $I_C = 10\ \text{mA}$	18	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	open collector; $I_E = 0.1\ \text{mA}$	3	–	–	V
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 28\ \text{V}$	–	–	20	μA
h_{FE}	DC current gain	$I_C = 150\ \text{mA}$; $V_{CE} = 5\ \text{V}$	25	80	–	
C_c	collector capacitance	$I_E = I_C = 0$; $V_{CB} = 10\ \text{V}$; $f = 1\ \text{MHz}$	–	2.5	–	pF
C_e	emitter capacitance	$I_C = I_E = 0$; $V_{EB} = 0.5\ \text{V}$; $f = 1\ \text{MHz}$	–	10.0	–	pF
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 10\ \text{V}$; $f = 1\ \text{MHz}$	–	1.5	–	pF
f_T	transition frequency	$I_C = 100\ \text{mA}$; $V_{CE} = 10\ \text{V}$; $f = 500\ \text{MHz}$; $T_{amb} = 25\ ^\circ\text{C}$	–	1.5	–	GHz
G_{UM}	maximum unilateral power gain note 1	$I_C = 100\ \text{mA}$; $V_{CE} = 10\ \text{V}$; $f = 500\ \text{MHz}$; $T_{amb} = 25\ ^\circ\text{C}$	–	10	–	dB

Note

- G_{UM} is the maximum unilateral power gain, assuming s_{12} is zero. $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)}\ \text{dB}$.

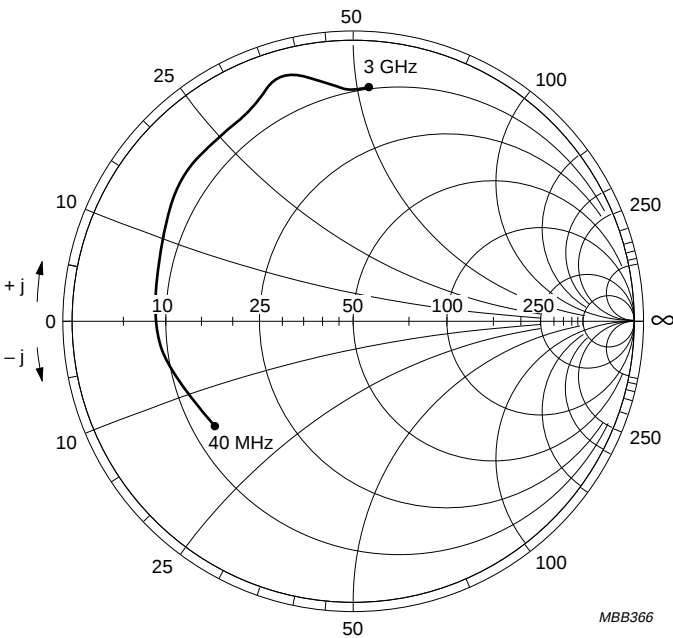
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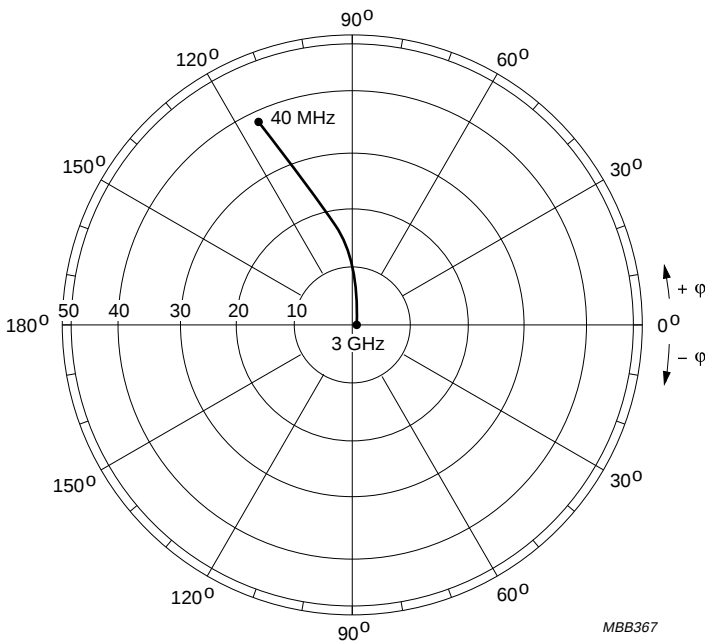
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$I_C = 70\text{ mA}$; $V_{CE} = 15\text{ V}$; $Z_0 = 50\ \Omega$.

Fig.6 Common emitter input reflection coefficient (S_{11}).

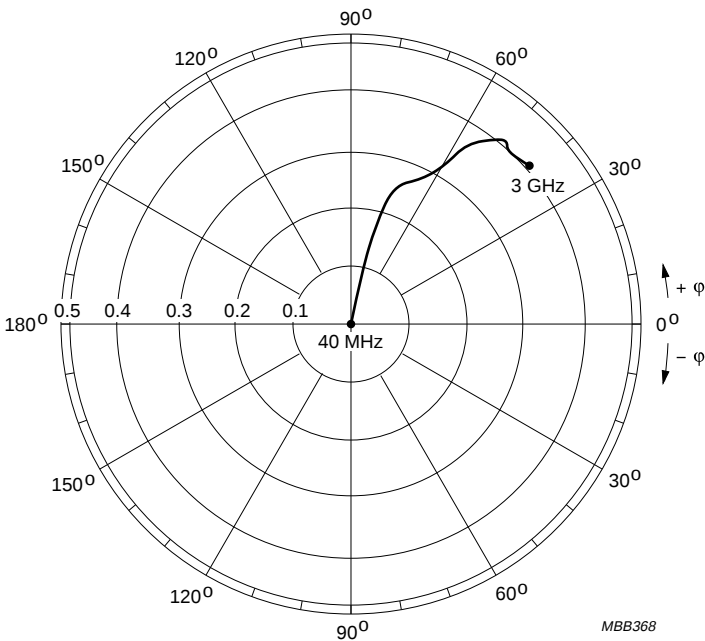


$I_C = 70\text{ mA}$; $V_{CE} = 15\text{ V}$.

Fig.7 Common emitter forward transmission coefficient (S_{21}).

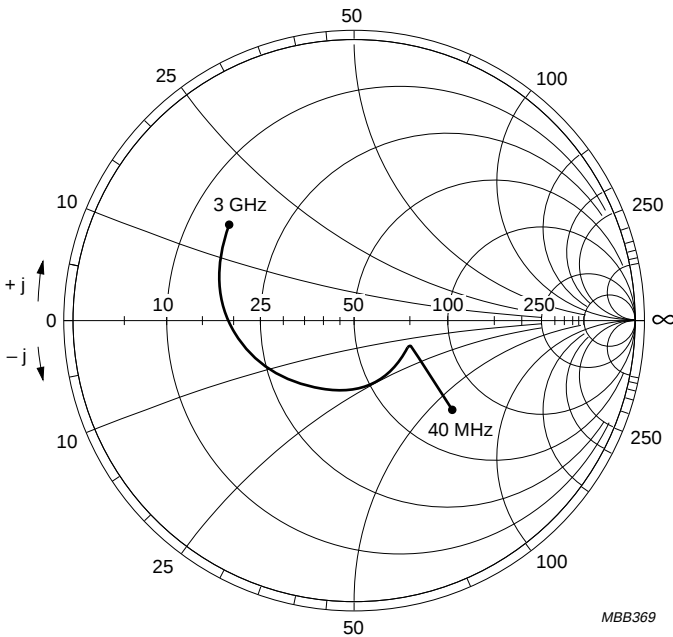
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$I_C = 70\text{ mA}$; $V_{CE} = 15\text{ V}$.

Fig.8 Common emitter reverse transmission coefficient (S_{12}).



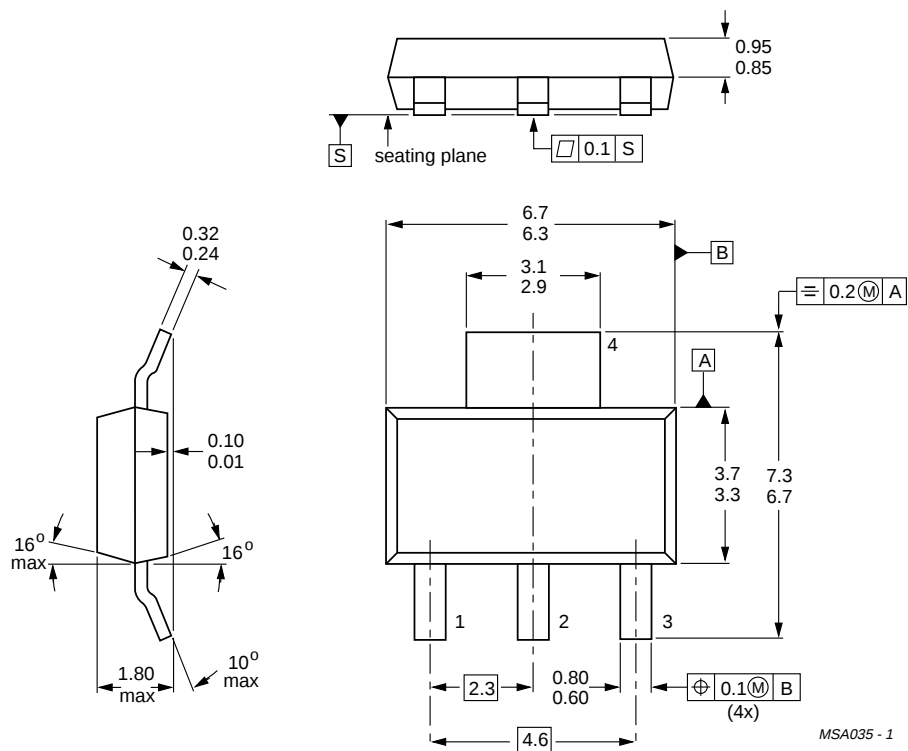
$I_C = 70\text{ mA}$; $V_{CE} = 15\text{ V}$; $Z_0 = 50\ \Omega$.

Fig.9 Common emitter output transmission coefficient (S_{22}).

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PACKAGE OUTLINE



Dimensions in mm.

Fig.10 SOT223.

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Short-form specification	The data in this specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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